



### N-CHANNEL ENHANCEMENT MODE MOSFET

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	6.0mΩ @ V <sub>GS</sub> = 10V	14.1A
24V	$7.2 \text{m}\Omega @ V_{GS} = 4.5 \text{V}$	12.9A
	12.5mΩ @ $V_{GS} = 2.5V$	9.8A

# **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- Battery Management Application
- Power Management Functions
- DC-DC Converters

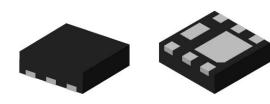
### **Features**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

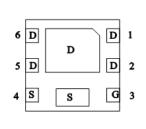
## **Mechanical Data**

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

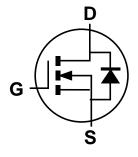
### U-DFN2020-6 (Type F)



Top View Bottom View



Pin Out Bottom View



Internal Schematic

# Ordering Information (Note 4)

Part Number	Case	Reel Size (inches)	Quantity per Reel
DMT2004UFDF-7	U-DFN2020-6 (Type F)	7	3,000
DMT2004UFDF-13	U-DFN2020-6 (Type F)	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Date Code Hoy												
Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		Е	F		G	Н			J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum** Ratings (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	24	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	14.1 11.2	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	70	Α		
Continuous Source-Drain Diode Current (Note 6)	Is	2	Α		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	26	Α		
Avalanche Energy (Note 7) L = 0.1mH	•		Eas	36	mJ

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	$P_{D}$	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	149	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	70	°C/W
Total Power Dissipation (Note 6)	$T_C = +25$ °C	$P_{D}$	12.5	W
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	12	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

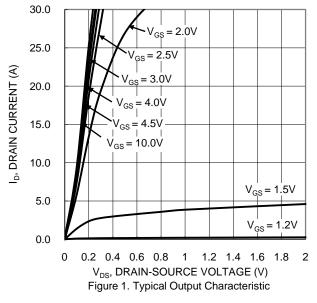
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	24	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current (T <sub>J</sub> = +25°C)	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.55	_	1.45	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	4.8	6		$V_{GS} = 10V, I_D = 9A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	5.8	7.2	mΩ	$V_{GS} = 4.5V, I_D = 8A$	
	, ,	_	9.6	12.5		$V_{GS} = 2.5V, I_D = 5A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.65	1.0	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	1683	_		45)/ 1/ 0)/	
Output Capacitance	Coss	_	581	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	559	_			
Gate Resistance	R <sub>G</sub>	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	29.6	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	53.7	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	4.2	_	nc	$V_{DD} = 15V, I_{D} = 9A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	13.4	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.9	_			
Turn-On Rise Time	t <sub>R</sub>	_	9.6	_		V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	30.8	_	ns	$R_G = 3\Omega$ , $I_D = 9A$	
Turn-Off Fall Time	t <sub>F</sub>	_	38.6	_			
Reverse Recovery Time	t <sub>RR</sub>	_	11.2	-	ns	1 4 5 4 11/11 400 4/11	
Reverse Recovery Charge	$Q_{RR}$	_	22.9	-	nC	$I_F = 1.5A$ , di/dt = 100A/ $\mu$ s	

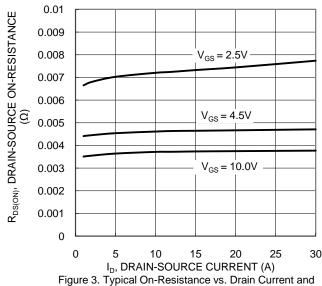
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

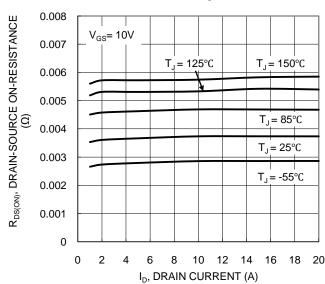
- 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25$ °C.
- S. Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.





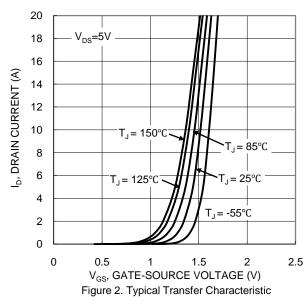


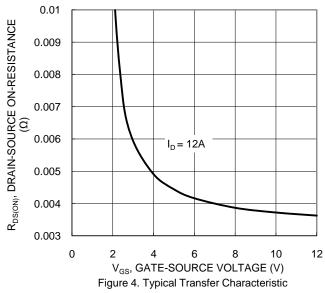




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature





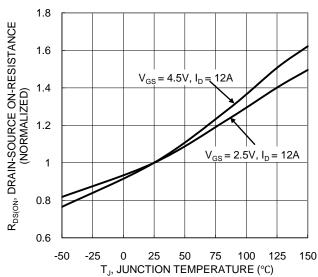


Figure 6. On-Resistance Variation with Temperature





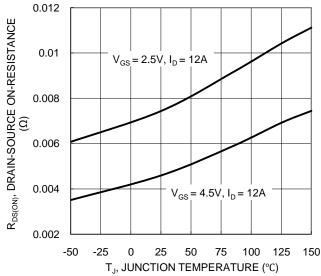
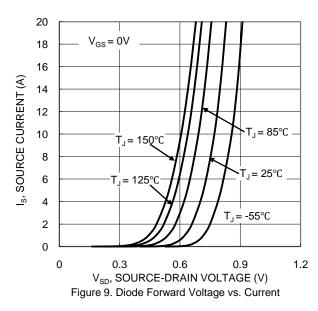
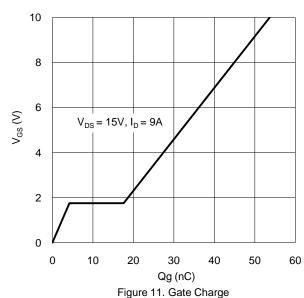


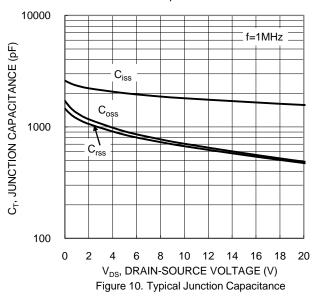
Figure 7. On-Resistance Variation with Temperature

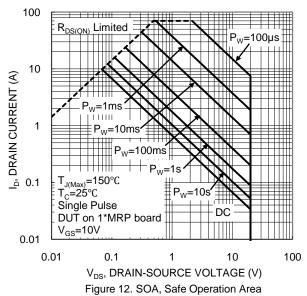




1.2  $V_{GS(TH)}$ , GATE THRESHOLD VOLTAGE (V) 1  $I_D = 1mA$ 0.8 0.6  $I_{D} = 250 \mu A$ 0.4 0.2 0 -50 -25 0 25 50 75 100 125 150  $T_J$ , JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature







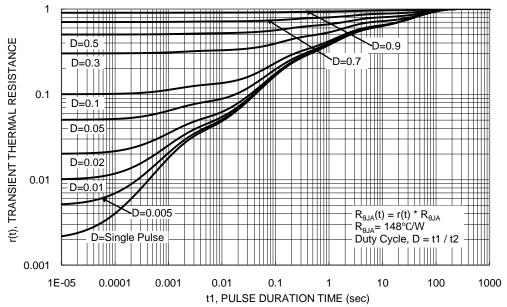


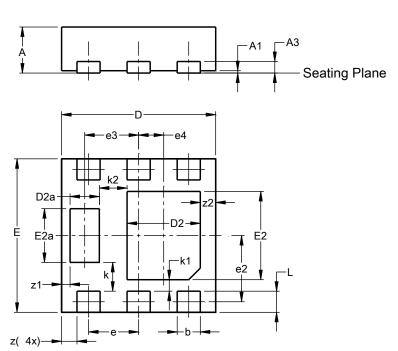
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## U-DFN2020-6 (Type F)

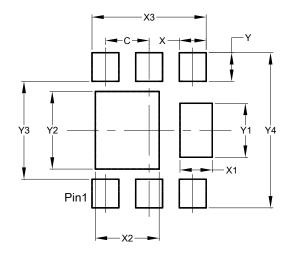


U-DFN2020-6								
(Type F)								
Dim	Min	Max	Тур					
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е		0.65 BS	С					
e2	C	).863 BS	SC SC					
е3		0.70 BS	С					
e4	C	).325 BS	SC SC					
k		0.37 BS	С					
k1	0.15 BSC							
k2	0.36 BSC							
L	0.225 0.325 0.275							
Z	0.20 BSC							
<b>z</b> 1	0.110 BSC							
z2	0.20 BSC							
All Dimensions in mm								

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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